2SD1978

Silicon NPN Epitaxial, Darlington

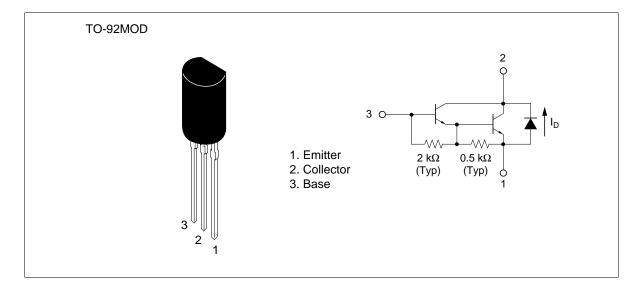
HITACHI

ADE-208-1162 (Z) 1st. Edition Mar. 2001

Application

- Low frequency power amplifier
- Complementary pair with 2SB1387

Outline





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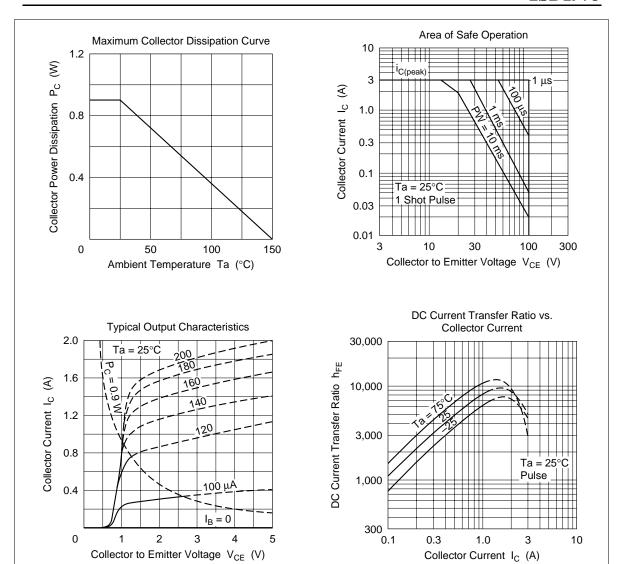
Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

| Item | Symbol | Ratings | Unit |
|------------------------------|------------------|----------------------|------|
| Collector to base voltage | V_{CBO} | 120 | V |
| Collector to emitter voltage | V _{CEO} | V _{CEO} 120 | |
| Emitter to base voltage | V_{EBO} | 7 | V |
| Collector current | I _c | 1.5 | A |
| Collector peak current | ic (peak) | 3.0 | А |
| Collector power dissipation | P _c | 0.9 | W |
| Junction temperature | Tj | 150 | °C |
| Storage temperature | Tstg | -55 to +150 | °C |
| E to C diode forward current | I _D | 1.5 | А |

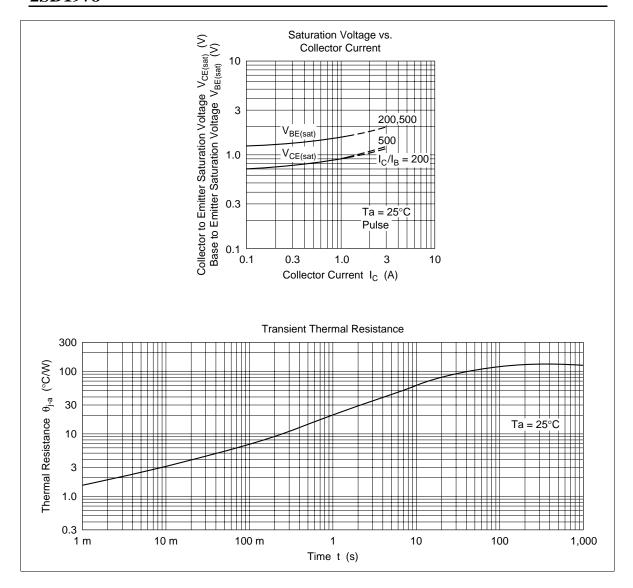
Electrical Characteristics ($Ta = 25^{\circ}C$)

| Item | Symbol | Min | Тур | Max | Unit | Test conditions |
|---|-----------------------|------|-----|-------|------|--|
| Collector to base breakdown voltage | $V_{(BR)CBO}$ | 120 | _ | _ | V | $I_{\rm C} = 0.1 \text{ mA}, I_{\rm E} = 0$ |
| Collector to emitter breakdown voltage | $V_{(BR)CEO}$ | 120 | _ | _ | V | I_{C} = 10 mA, R_{BE} = ∞ |
| Emitter to base breakdown voltage | $V_{(BR)EBO}$ | 7 | _ | _ | V | $I_{\rm E} = 50 \text{ mA}, I_{\rm C} = 0$ |
| Collector cutoff current | I _{CBO} | _ | _ | 1.0 | μΑ | $V_{CB} = 100 \text{ V}, I_{E} = 0$ |
| | I _{CEO} | _ | _ | 10 | μΑ | V _{CE} = 100 V, R _{BE} = ∞ |
| DC current transfer ratio | h_{FE} | 2000 | _ | 30000 | | $V_{CE} = 3 \text{ V}, I_{C} = 1 \text{ A}^{*1}$ |
| Collector to emitter saturation voltage | $V_{\text{CE(sat)1}}$ | _ | _ | 1.5 | V | $I_C = 1 \text{ A}, I_B = 1 \text{ mA*}^1$ |
| | V _{CE(sat)2} | _ | _ | 2.0 | V | $I_{\rm C} = 1.5 \text{ A}, I_{\rm B} = 1.5 \text{ mA}^{*1}$ |
| Base to emitter saturation voltage | $V_{BE(sat)1}$ | _ | _ | 2.0 | V | $I_C = 1 \text{ A}, I_B = 1 \text{ mA}^{*1}$ |
| | $V_{BE(sat)2}$ | _ | _ | 2.5 | V | $I_{\rm C}$ = 1.5 A, $I_{\rm B}$ = 1.5 mA* ¹ |
| E to C diode forward voltage | V_{D} | _ | _ | 3.0 | V | I _D = 1.5 A* ¹ |

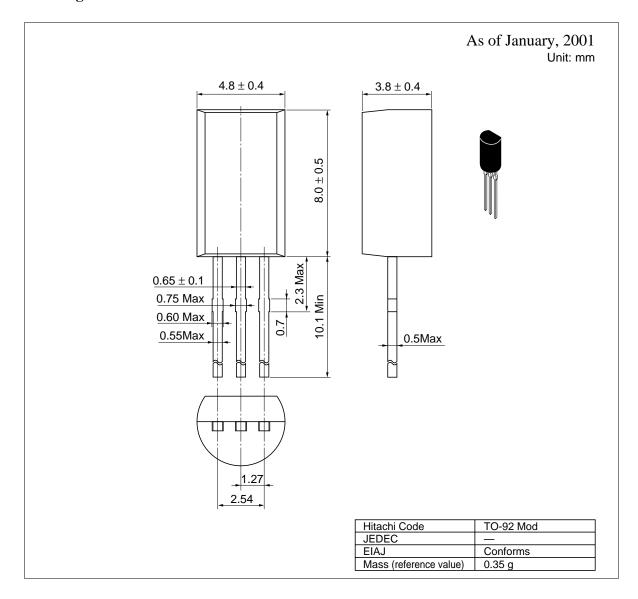
Note: 1. Pulse test



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Package Dimensions



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